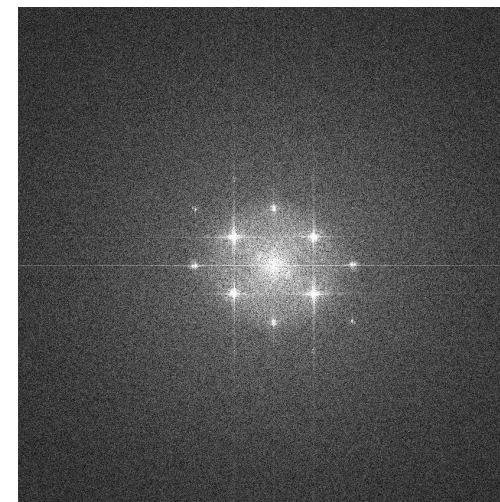
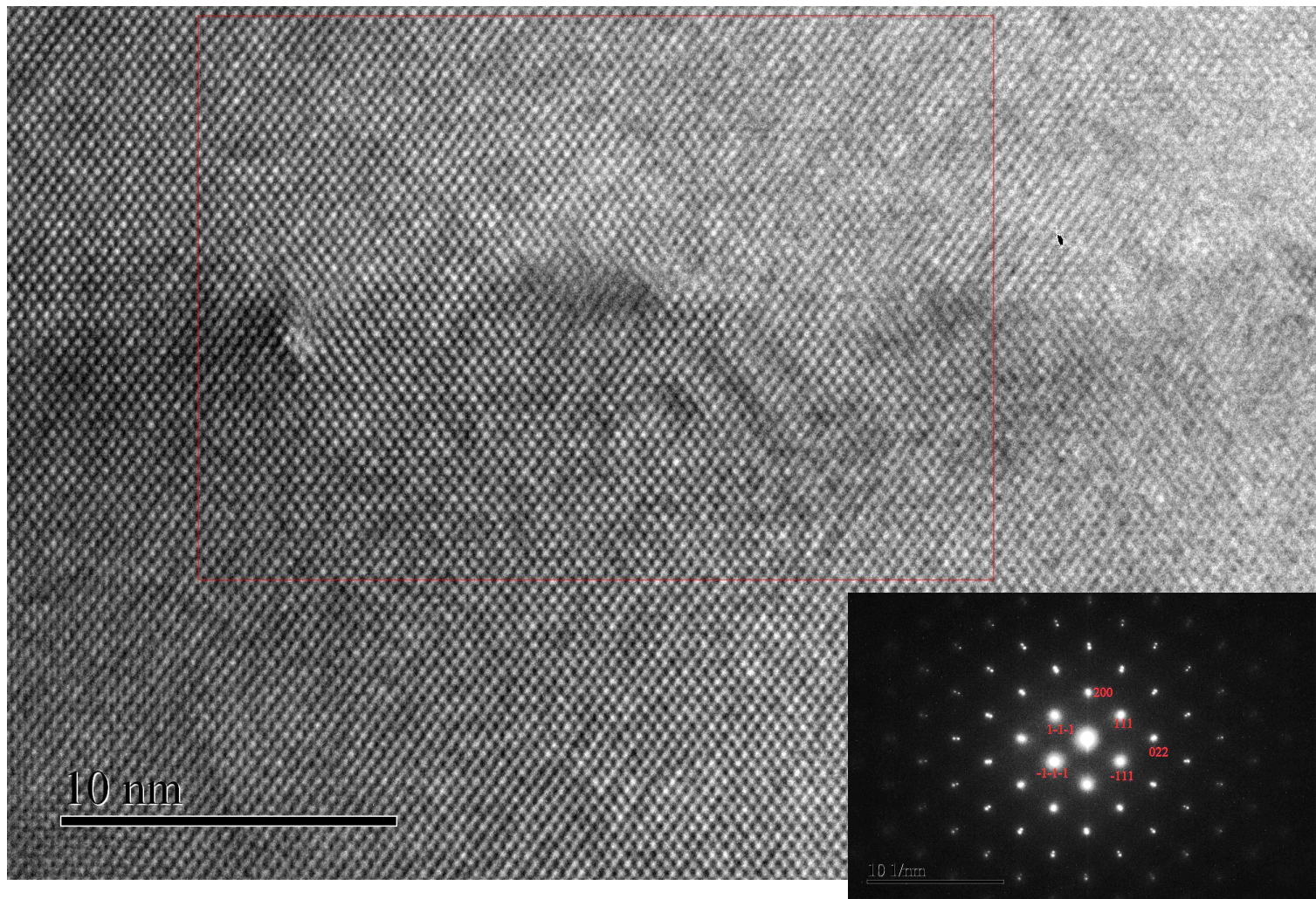


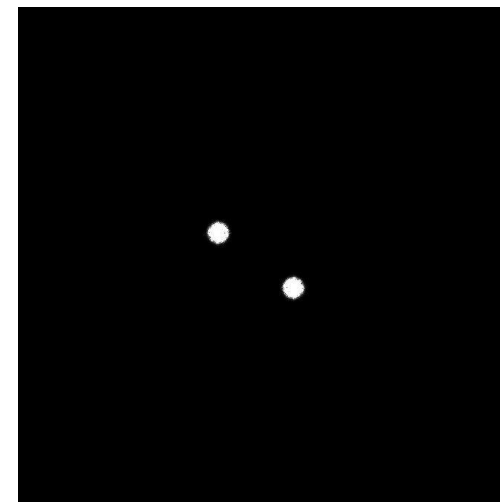
# Section 0.1.6 FFT Analysis

InAs

InP



FFT from red box



Masked FFT



2519465  
2519466  
2519467



THE UNIVERSITY  
of NORTH CAROLINA  
at CHAPEL HILL

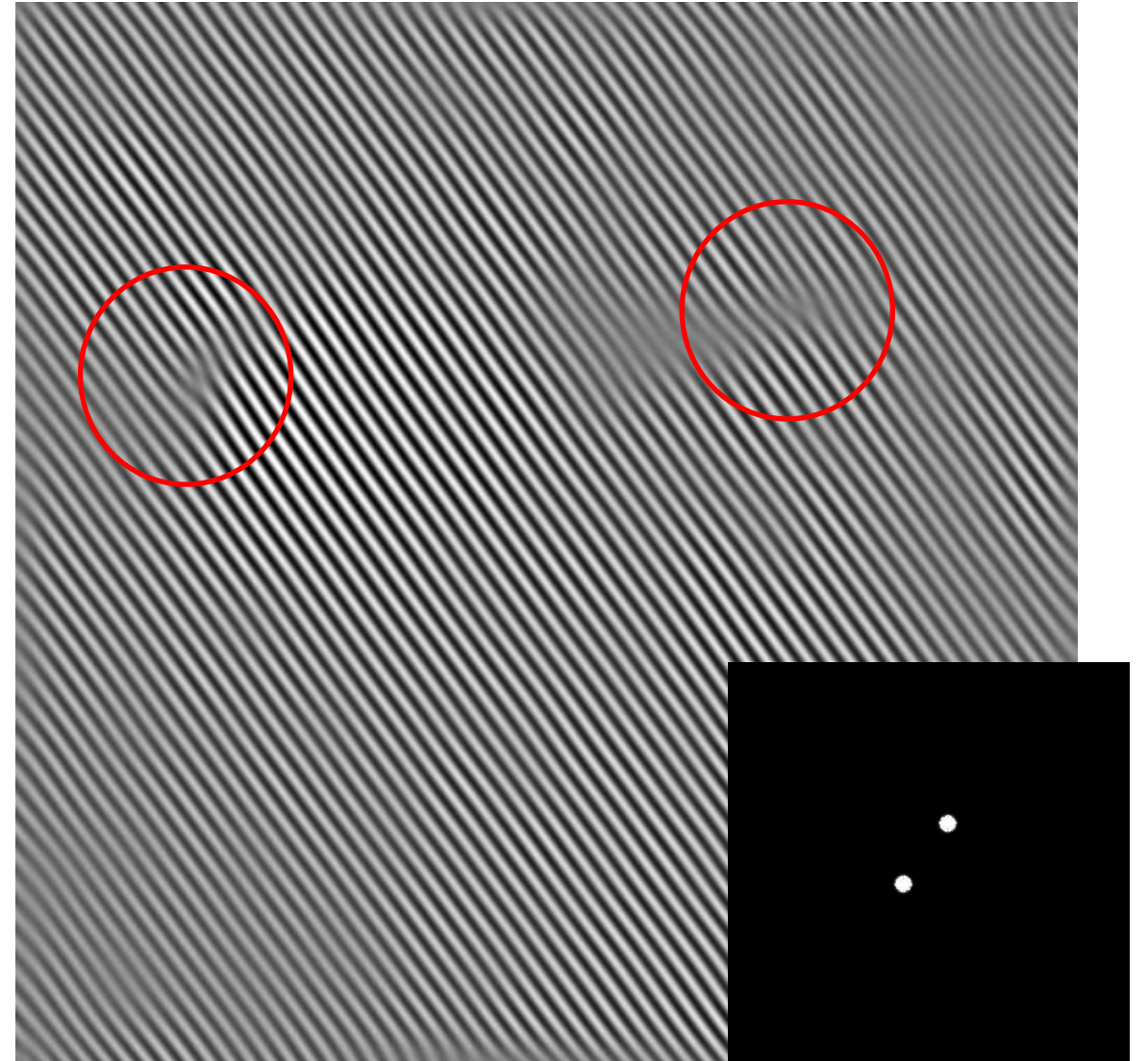
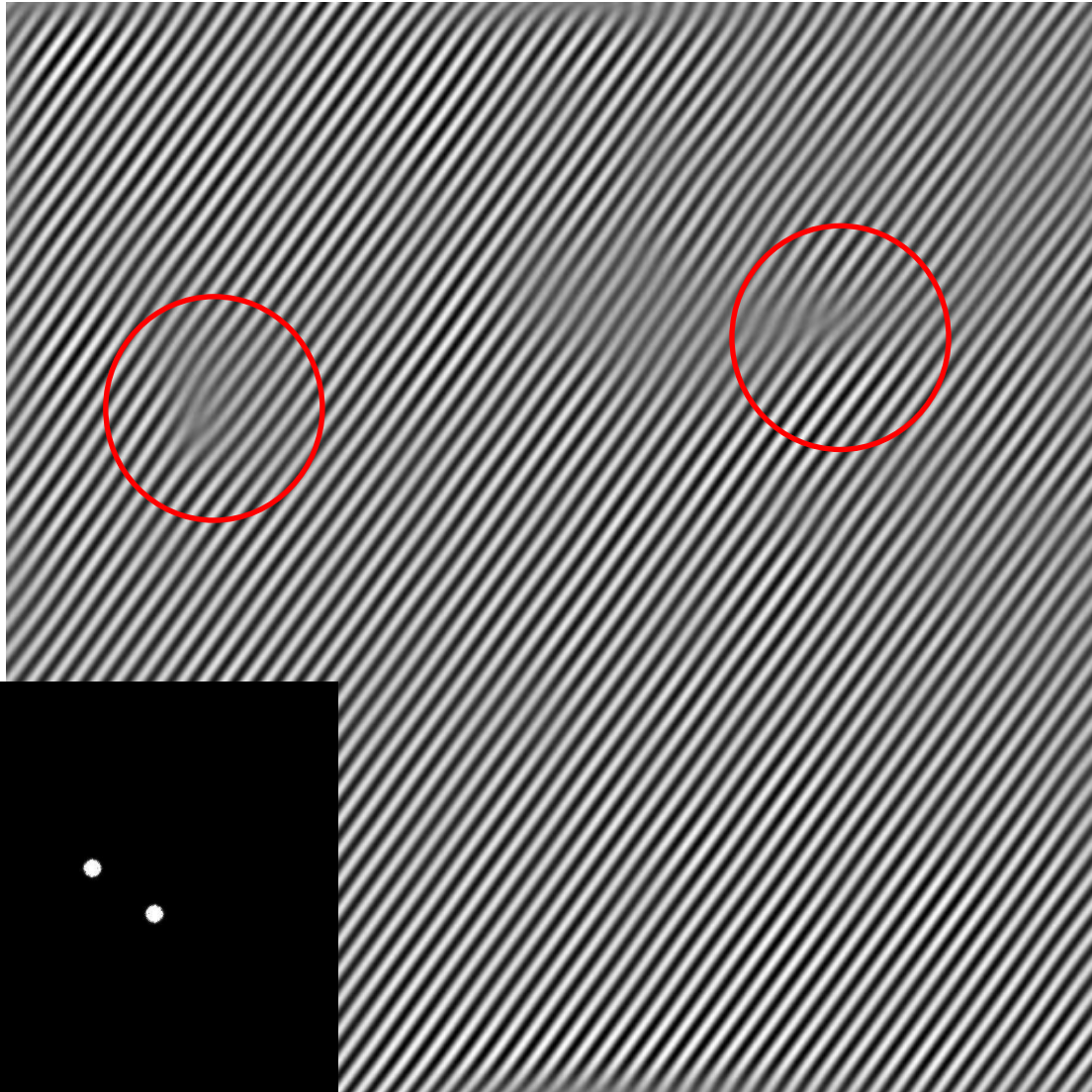


UNIVERSITY OF  
MARYLAND

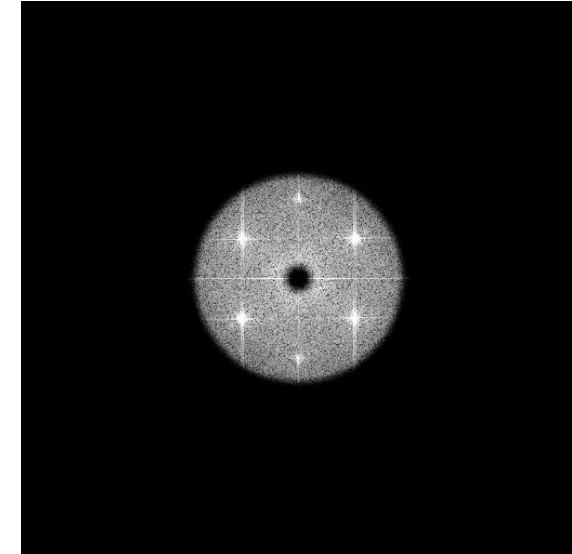
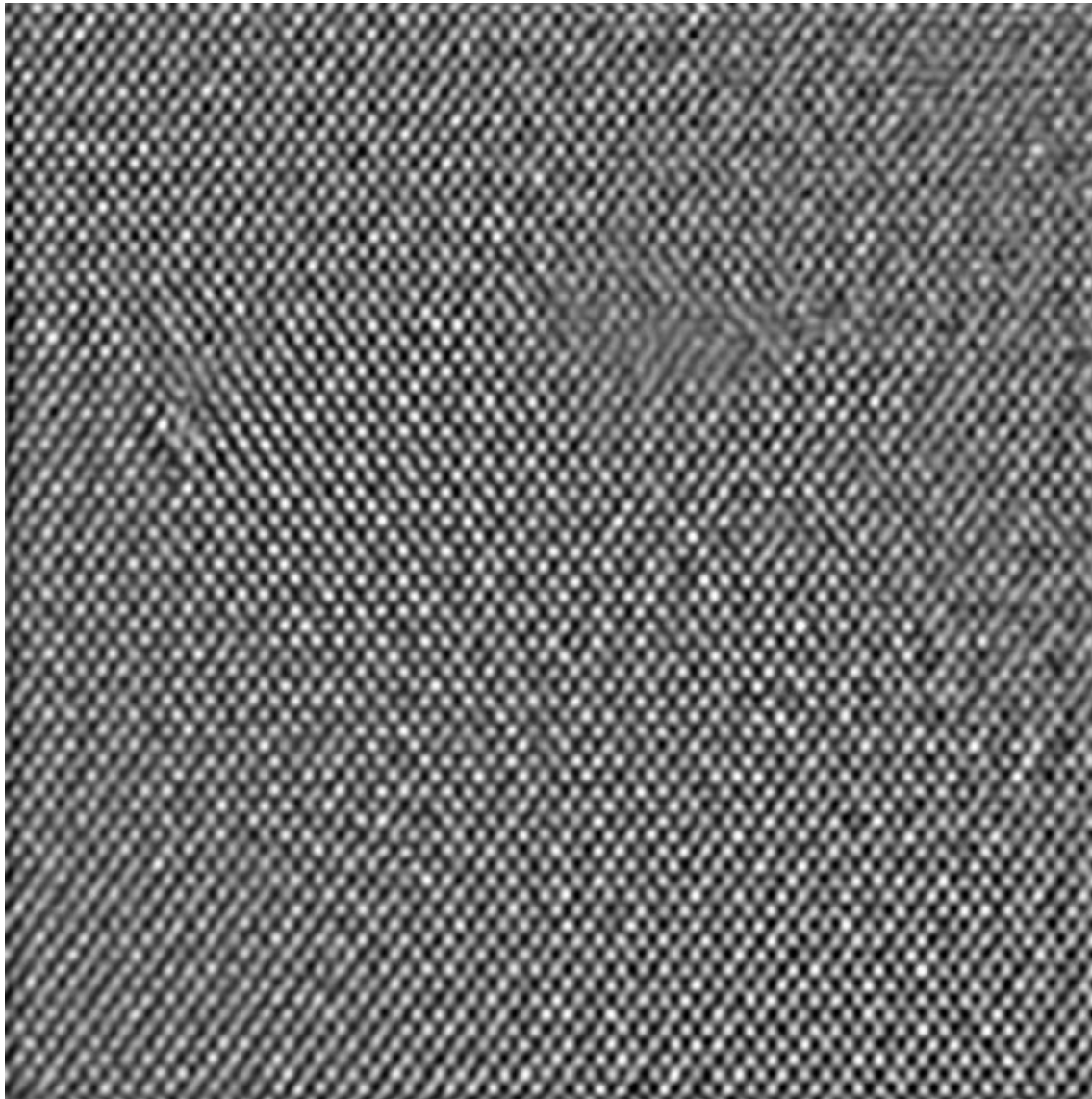


USC University of  
Southern California

# Inverse FFT (IFFT) Ba(Sr) TiO<sub>3</sub> Misfit Dislocations

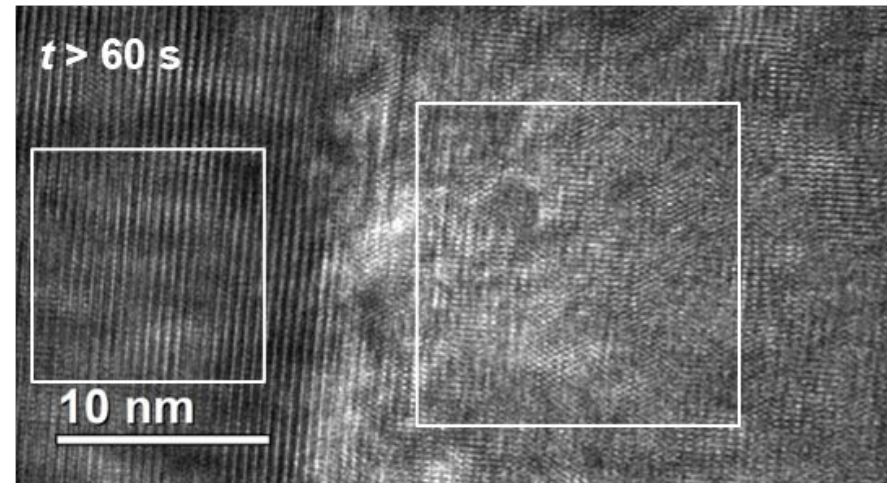
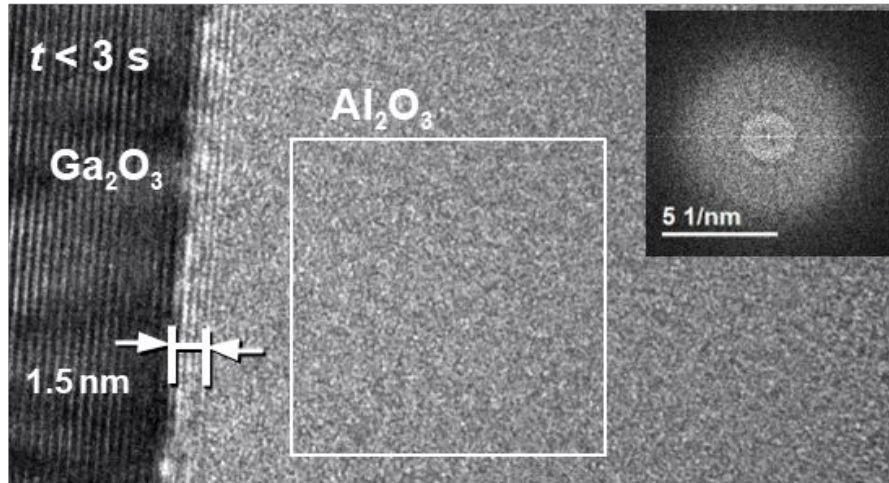


# IFFT to Enhance Contrast Filter out noise

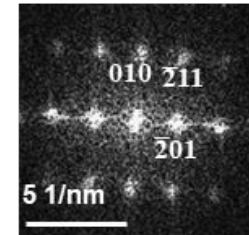


Annular filter

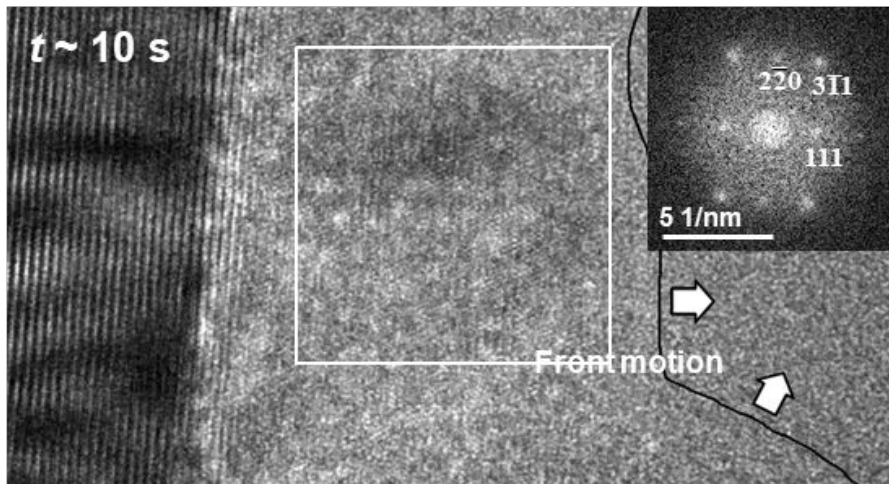
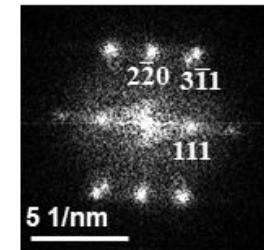
# Electron Beam-induced Crystallization $\text{Ga}_2\text{O}_3/\text{Al}_2\text{O}_3$



© [102]  $\text{Ga}_2\text{O}_3$



© [11 $\bar{2}$ ]  $\gamma\text{-Al}_2\text{O}_3$



- $\text{Al}_2\text{O}_3$  layers crystallized fully after several seconds of TEM beam exposure, outward from interface (not from the Al contact, or homogeneously)
- Each of 3 samples showed the same qualitative effect, including one already annealed at  $500^\circ \text{C}$